

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

DC4927

Application Number

to be assigned

Applicant(s)

Boisvert et al.

Filing Date

to be assigned

Group Art Unit

1712 to be assigned

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	IF APPROPRIATE
KMP		3,615,272	10/26/1971	Collins et al.	023	366	
		4,756,977	07/12/1988	Haluska et al.	428	704	
		5,446,088	08/29/1995	Haluska	524	588	
		6,022,814	02/08/2000	Mikoshiba et al.	438	789	
		6,231,989	05/15/2001	Chung et al.	428	447	

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
KMP		WO 98/49721	5NOV1998	PCT	H01L	21/316		
		5-333553	19931217	Japan	G03F	7/075	✓	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

KMP		JOURNAL OF MATERIALS CHEMISTRY; "Preparation of low density poly (methylsilsequioxane)s for LSI interlayer dielectrics with low dielectric constant. Fabrication of Angstrom size pores prepared by baking trifluoropropylsilyl copolymers", Satoshi Mikoshiba and Shuzi Hayase, 1999, 9, 591-598.

EXAMINER

KMP

DATE CONSIDERED

8/17/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.